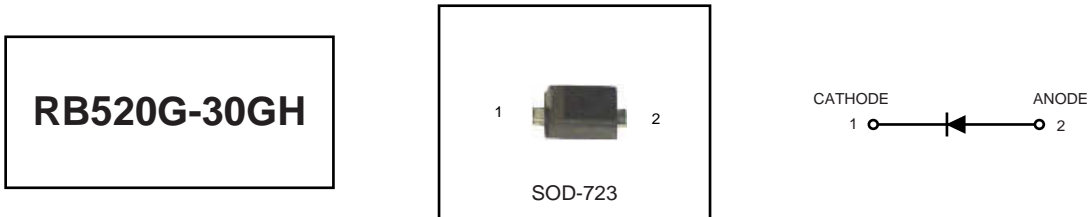


## Schottky Barrier Diode

- \* Halogen-free type
- \* Lead free product
- \* Small surface mounting type
- \* Low reverse current and low forward voltage
- \* High reliability



### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Maximum Recurrent Peak Reverse Voltage	VRRM	30	V
Maximum Average Forward Rectified Current	I <sub>o</sub>	100	mA
Peak Forward Surge Current at 8.3 mSec single half sine-wave	I <sub>FSM</sub>	500	mA
Maximum Junction Temperature Range	T <sub>J</sub>	+125	
Storage Temperature Range	T <sub>STG</sub>	-40 to +125	

### DEVICE MARKING

**RB520G-30GH = E**

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

Maximum Instantaneous Forward Voltage at I <sub>F</sub> =10mA	V <sub>F</sub>	0.45	V
Maximum Average Reverse Current at V <sub>R</sub> =10V	I <sub>R</sub>	0.5	μA

FIG. 1 - FORWARD CHARACTERISTICS

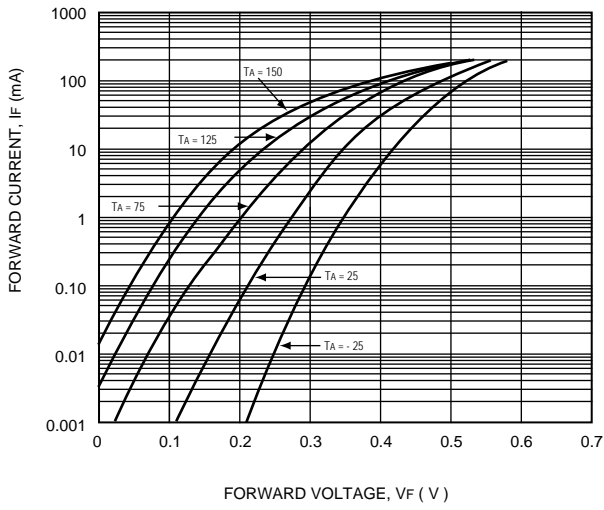


FIG. 2 - REVERSE CHARACTERISTICS

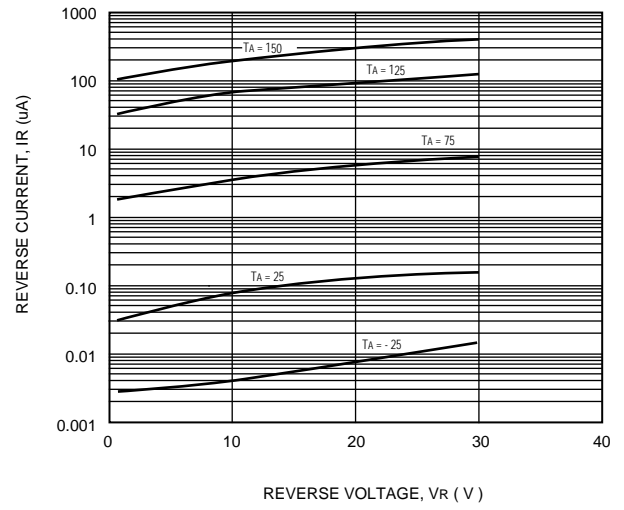
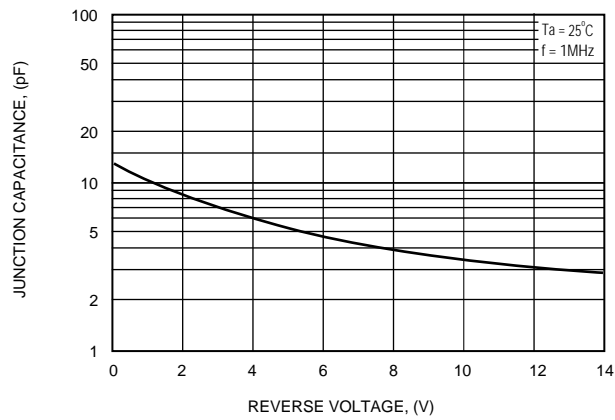
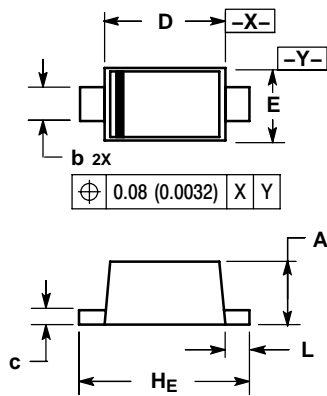


FIG. 3 - TYPICAL JUNCTION CAPACITANCE



## CASE DRAWINGS

### SOD-723



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.49	0.52	0.55	0.019	0.020	0.022
b	0.25	0.28	0.32	0.0098	0.011	0.013
c	0.08	0.12	0.15	0.0032	0.0047	0.0059
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.55	0.60	0.65	0.022	0.024	0.026
$H_E$	1.35	1.40	1.45	0.053	0.055	0.057
L	0.15	0.20	0.25	0.006	0.0079	0.010

### SOLDERING FOOTPRINT\*

